



SW Test Workshop

Semiconductor Wafer Test Workshop

June 7 - 10, 2015 | San Diego, California

An probing evaluation of Cu-Pillar by using wire type Probe Card



Chang-Hoon, Hyun
Samsung Electronics

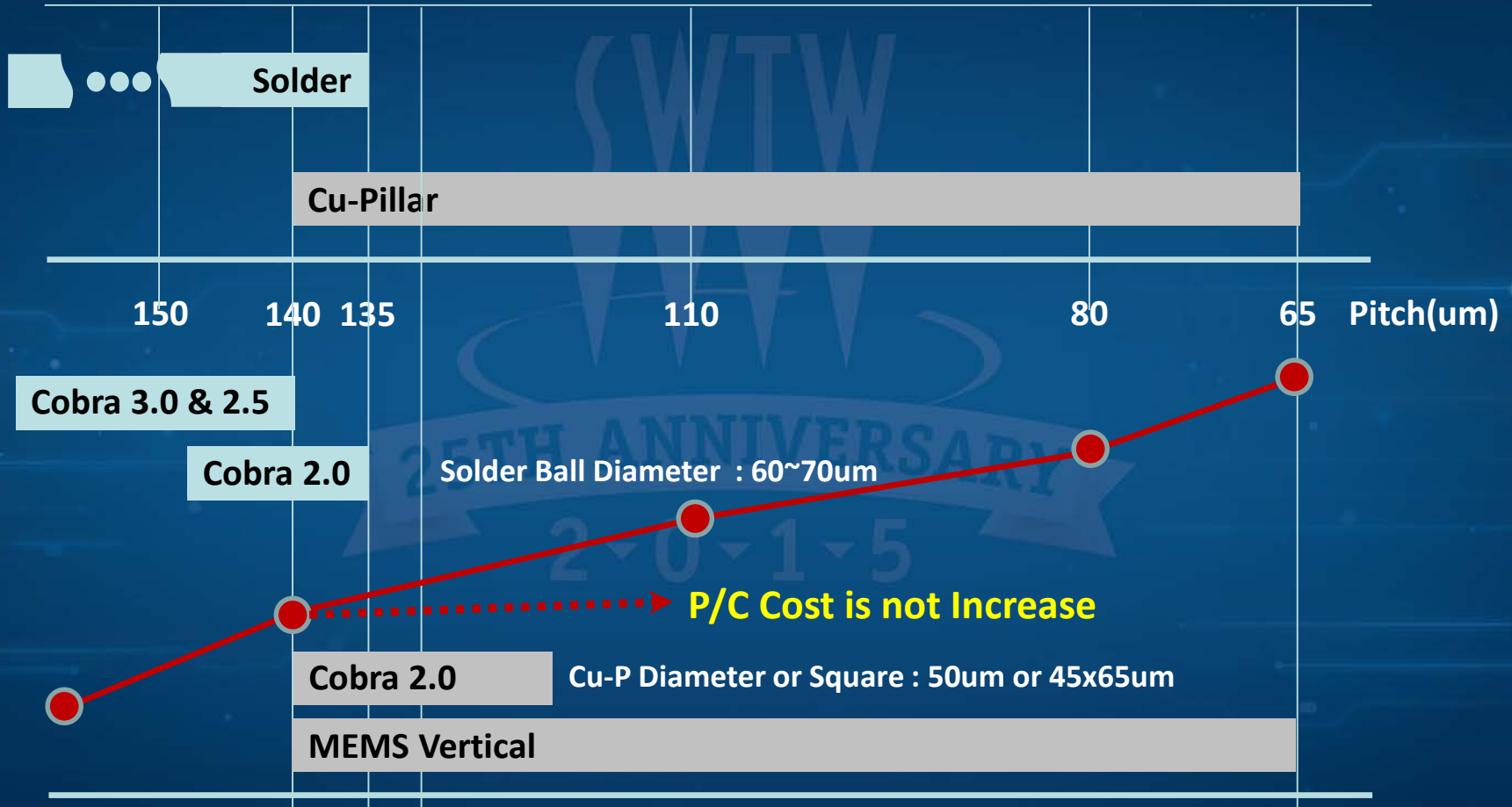


Contents

- Probe Card cost of Cu-Pillar probing
- Cases introduction of Cu-Pillar probing
 - Temperature & Pad structure
- An experience of Cu-Pillar probing by wire type
- Process change for cost reduction
- SEC Requirement of Cu-Pillar Flip-Chip Probing
- Probe Card long life (MEMS Vertical)
- Summary

Probe Card cost for Cu-P probing

※ Cu-Pillar = Cu-P

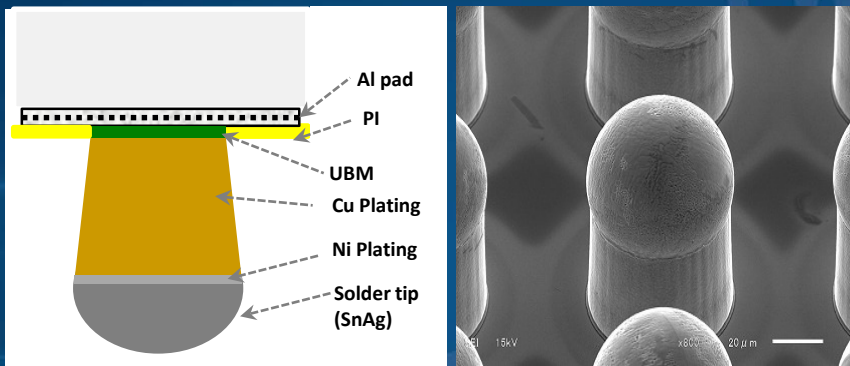


※ The using of Cu-P is increasing in the DTV controller & lower MoDAP chips
 → P/C cost is very important for higher margin of revenue

Test case of Cu-P probing

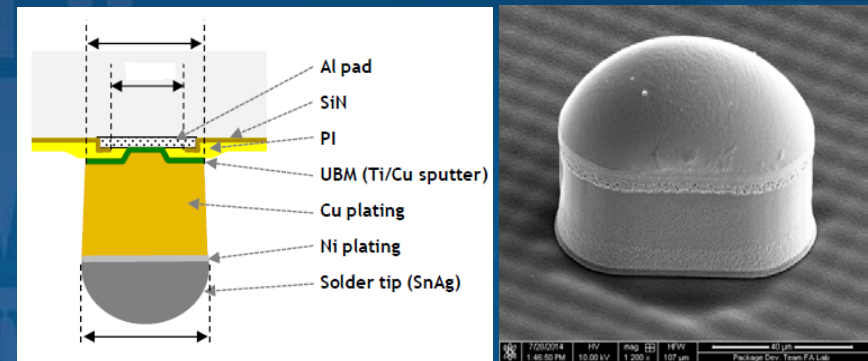
A. Cu-P Structure Introduction

TCFC : Thermal Compression Flip Chip



Source : DIPSOL Website Figure
http://www.dipsol-jp.com/wp-content/uploads/bump_reflow_sem200.png

CuBOL : Copper-column Bond on Lead



Source : Hamid Eslampour(STATSChipPAC)
“Low Cost Cu Colimn fcPOP Technology “
IEEE, EMTC, 2012

- The diameter limit of CuBol type is 40~45um → **100um under pitch will be used TCFC**
- Cu-P is expected to grow at CAGR(2014~2018) of 10~15% (SEC Case)
 - 2014 ~ 2015 : **28nm Controller/Modem (Room Temp)** & MoDAP (Hot Temp)
 - 2016 ~ 2018 : 10~14nm Premium AP & **28nm Product(~beyond)**
 - Mobile Phone Price drop down → Improve PKG Cost → Applying of Cu-P will expand

Test case of Cu-P probing

B. Cu-P Products Table

Room : 77°F, Hot : 185°F

Type	Diameter (um)	Temperature (°F)	Product	Probe Card Type
CuBOL	45 x 65	Room	Controller , Modem	Cobra - 2.0mil
		Room/Hot	Premium AP, MoDAP	MEMS Vertical
TCFC	50	Room	Foundry	Cobra - 2.0mil
		Room/Hot	Premium AP, MoDAP	MEMS Vertical
	30	Room	Foundry	MEMS Vertical
		Room/Hot	Premium AP, MoDAP	

Probing Consideration

- In case of same tip force(O/D), impact on solder cap is different between Room and Hot temperature
- The key factors of our chip package process are **Height Variance and Stick Out** of Pillar

→ If Cu-P will be probing at room temperature, more higher force tip is able to use

Evaluation result by using wire type

A. Experiment Set-up

- **Test Wafer Descriptions**

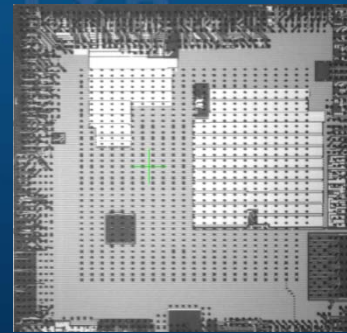
- . Real Function Wafers of DV Controller : Peripheral Cu-Pillar
- . 135um Minimum Pitch
- . Cu-Pillar Type : Cu-BOL (45x65um)

- **Probe Card Used**

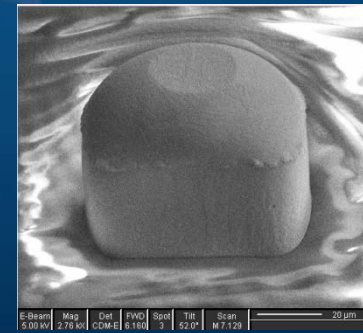
- . Will Technology Cobra 2.0 Probe Card (& developed MEMS Vertical)
- . Cobra 2.0mil / 3,908pins / 2 Para

- **Measurement Condition**

- . Tester : T2K 8" Pogo Tower (ADVAN)
- . Prober : IP-300H (SECRON)
- . Image Capture : 3D Scope & FIB
- . Pillar Profile : 3D Scope



Test Chip Map

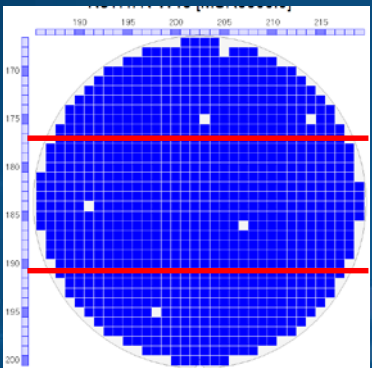
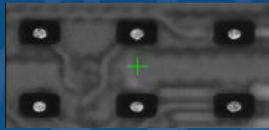
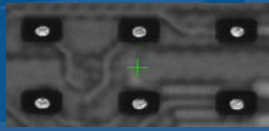
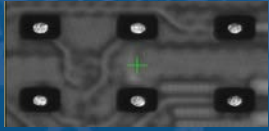
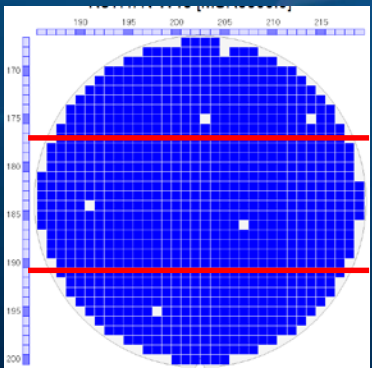
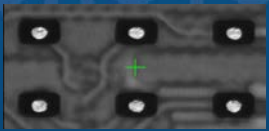
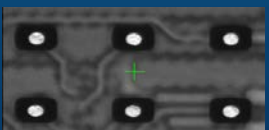



Cu-P With SnAg Caps

Evaluation result by using wire type

B. Probing DOE Result Table



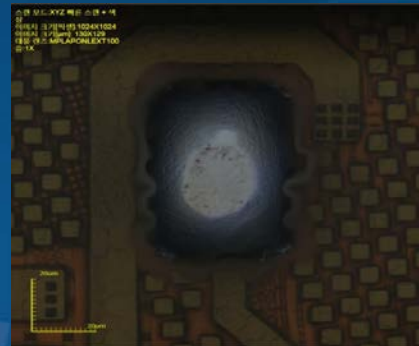
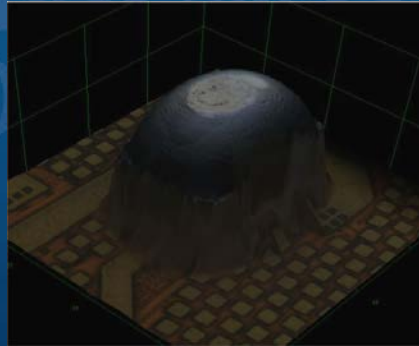
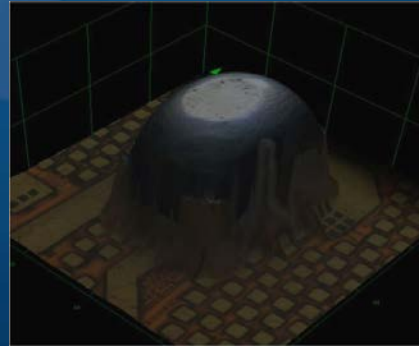
(Probing Condition : 6 Times Probing per 1 Cap)

Sample	DOE Map	Overdrive (um)	Image	Bump Height (um)		Mark Ratio (%)
				Before → After	Variance	
#1	 <p>Operation Condition</p>	70		61.7 → 60.2	1.5	10.7 ~ 13.0
		80		61.0 → 59.3	1.7	10.7 ~ 14.2
		90		61.8 → 59.8	2.0	11.8 ~ 15.2
#2	 <p>Overdrive Margin</p>	100		61.4 → 59.1	2.3	15.5 ~ 16.8
		110		61.2 → 58.6	2.6	15.5 ~ 18.1
		120		61.3 → 58.5	2.8	15.5 ~ 18.3

Evaluation result by using wire type

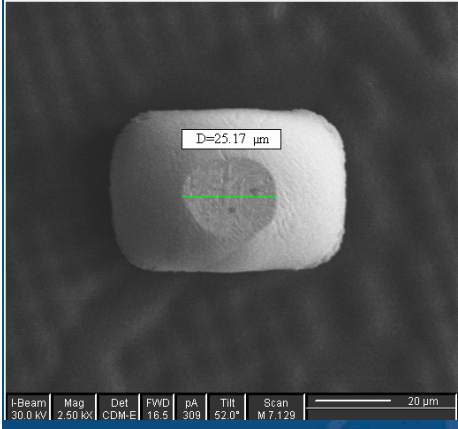
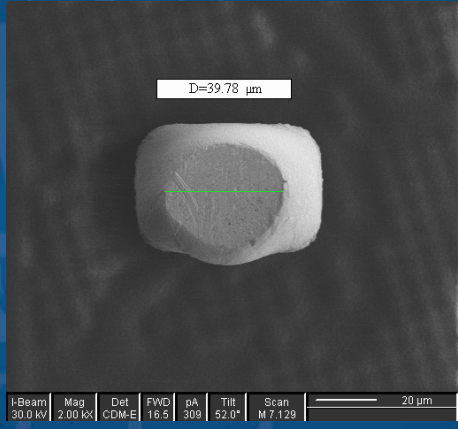
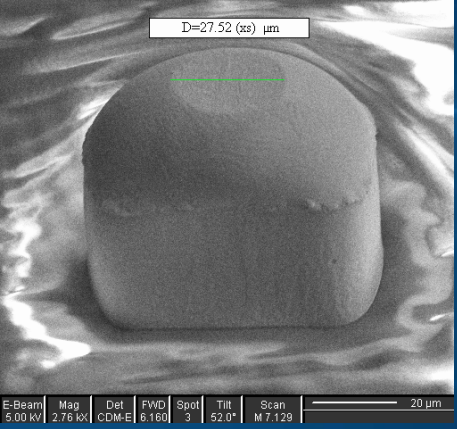
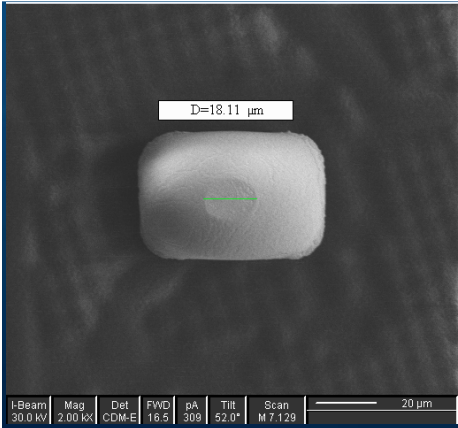
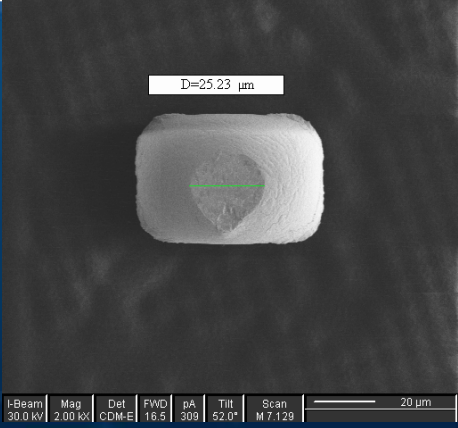
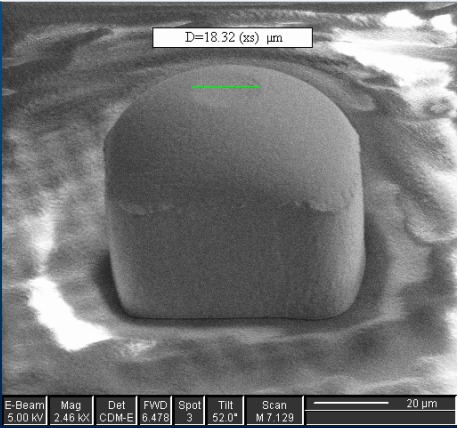
C. 3D Scope Image : Production Product

Room : 77°F

	80um	100um	120um
Top View			
Side View			
Measure	Probe X : 17.2um Probe Y : 22.9um Bump Z : 63.8um	Probe X : 20.3um Probe Y : 23.7um Bump Z : 61.3um	Probe X : 22.3um Probe Y : 27.4um Bump Z : 60.8um

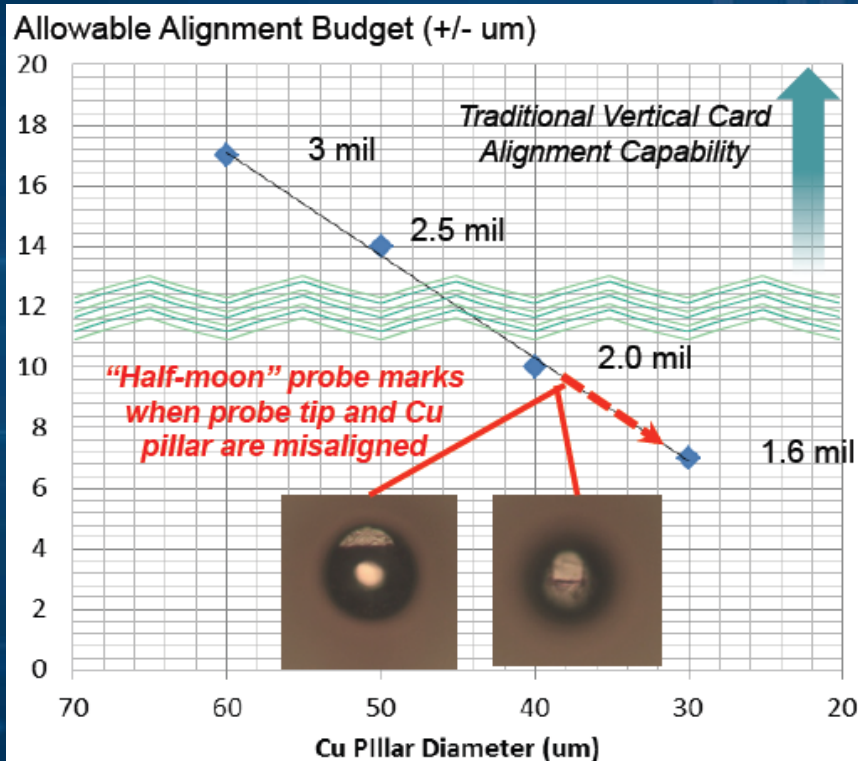
Evaluation result by using wire type

D. FIB Image : Cobra vs MEMS Vertical Probe

Overdrive (120um)	Temperature		Side View (77°F)
	77°F (25°C)	257°F (85°C)	
Cobra 2.0			
	<p>I-Beam 30.0 kV Mag 2.50 kx Det CDM-E FWD 16.5 pA 309 Tilt 52.0° Scan M 7.129 20 μm</p>	<p>I-Beam 30.0 kV Mag 2.00 kx Det CDM-E FWD 16.5 pA 309 Tilt 52.0° Scan M 7.129 20 μm</p>	<p>E-Beam 5.00 kV Mag 2.76 kx Det CDM-E FWD 6.160 Spot 3 Tilt 52.0° Scan M 7.129 20 μm</p>
	D=25.17 μm	D=39.78 μm	D=27.52 (ss) μm
MEMS			
	<p>I-Beam 30.0 kV Mag 2.00 kx Det CDM-E FWD 16.5 pA 309 Tilt 52.0° Scan M 7.129 20 μm</p>	<p>I-Beam 30.0 kV Mag 2.00 kx Det CDM-E FWD 16.5 pA 309 Tilt 52.0° Scan M 7.129 20 μm</p>	<p>E-Beam 5.00 kV Mag 2.46 kx Det CDM-E FWD 6.478 Spot 3 Tilt 52.0° Scan M 7.129 20 μm</p>
	D=18.11 μm	D=25.23 μm	D=18.32 (ss) μm

Evaluation result by using wire type

E. Pin Alignment & Plate Hole Processing Improvement



Source : Alexander Wittig(Global Foundry)
 "Probing Study of Fine Pitch Copper Pillars " SWTW 2013

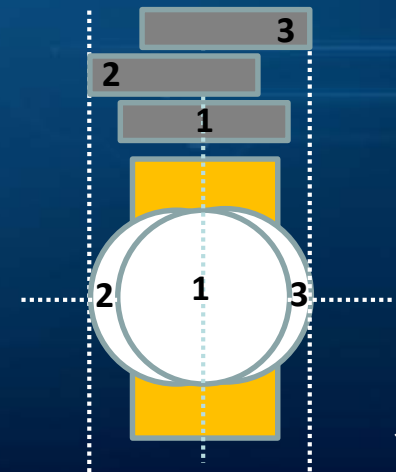
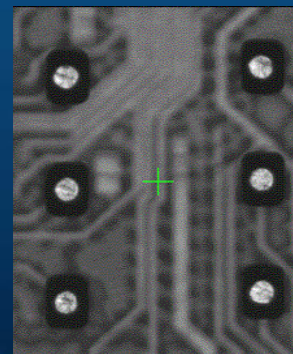
A. The key Items of Probe tip Alignment

1. Guide Plate Hole diameter & alignment
2. The range of Alignment fluctuation

B. 45x65um CuBOL probing

1. Alignment Budget Target : $\pm 10\mu\text{m}$
2. Hole diameter : Target $\pm 4\mu\text{m}$
3. Hole alignment : Target $\pm 2\mu\text{m}$
4. Probe tip alignment : $\pm 6\mu\text{m}$

Cobra2.0 – OD 5mil

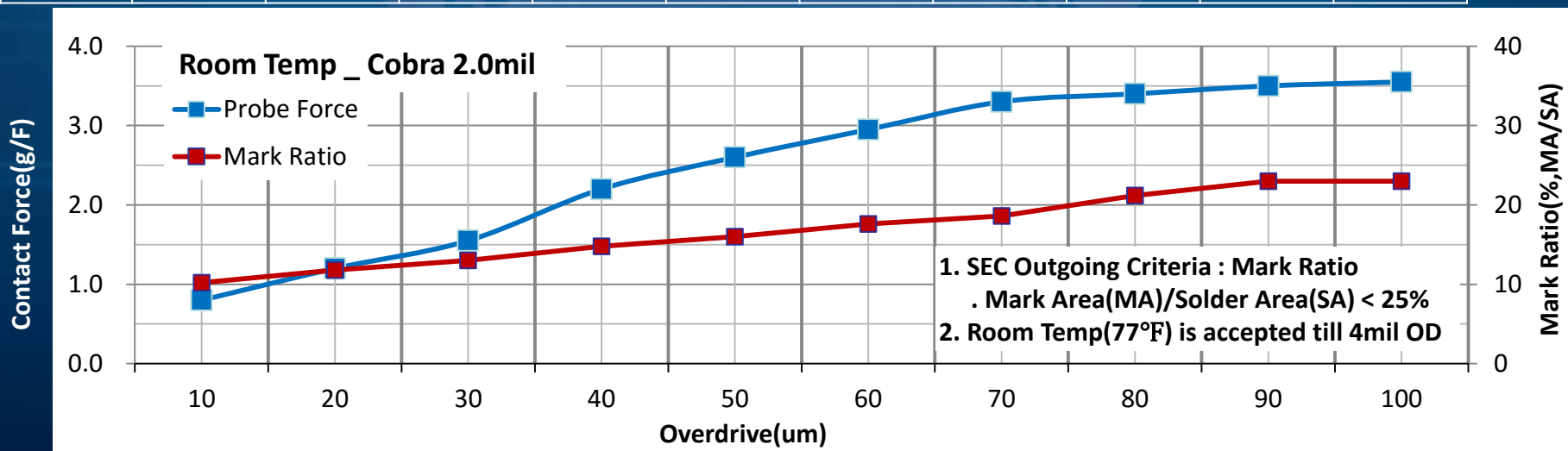


Evaluation result by using wire type

F. Tip Force & Optical Mark Image(For TCFC Type)

Cu-P Diameter : 50um

Temp	10um	20um	30um	40um	50um	60um	70um	80um	90um	100um
Room										
	10.2%	11.8%	13.0%	14.8	16.0%	17.6%	18.6%	21.2%	23.0%	23.0%
Hot										
	10.2%	12.5%	14.4%	19.4%	21.2%	23.0%	27.0%	31.4%	33.6%	36.0%

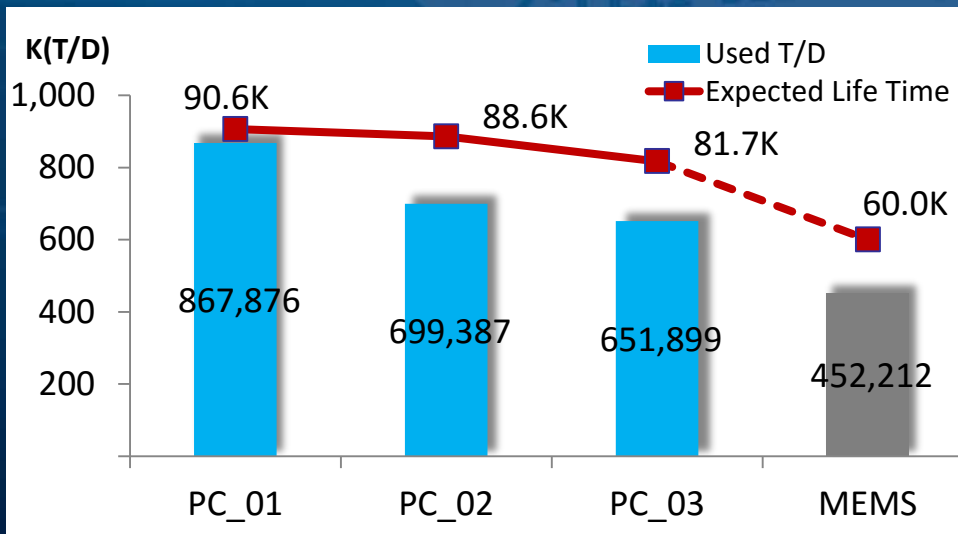


Evaluation result by using wire type

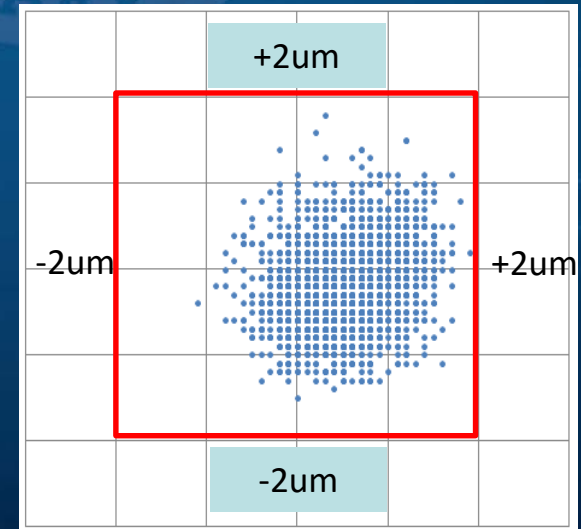
G. Cobra 2.0 Achievement

- **Cobra 2.0 vertical probe cards are more longer life time than MEMS vertical probe cards**
 - . Test Environment - 45um Over Diameter Solder Cap, Room Temperature – Can use Cobra 2.0
 - . **7~8\$/pin Cost Reduction** : Needle Cost + Extension Life time (SEC Case)
- **Cobra style vertical probe card challenges needle alignment**
 - . By improvement of plate processing, **in less than $\pm 6\mu\text{m}$ Alignment achievement**

Life Time Improve (vs MEMS – 1.5~2.0x)

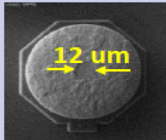


X/Y Plate Hole Alignment (Target $\pm 2\mu\text{m}$)



Process change for cost reduction

A. Cu-Pillar without Solder Cap

Probing Challenges	Tougher than Solder
Scheme	 <p>12 um</p> <p>Small Probe Mark</p>
Effects on Probing	<ol style="list-style-type: none"> 1. Hard to probe deeply 2. Small probe mark for inspection
Solutions	<ol style="list-style-type: none"> 1. Probe tip type selection 2. Probe force optimization

Source : Hao Chen(TSMC)

“Wafer Level Chip Scale Package Copper Pillar Probing”
International Test Conference 2014, Seattle, Washington

Cu Pillar without solder cap is a cheaper contact interface for InFO-PoP!

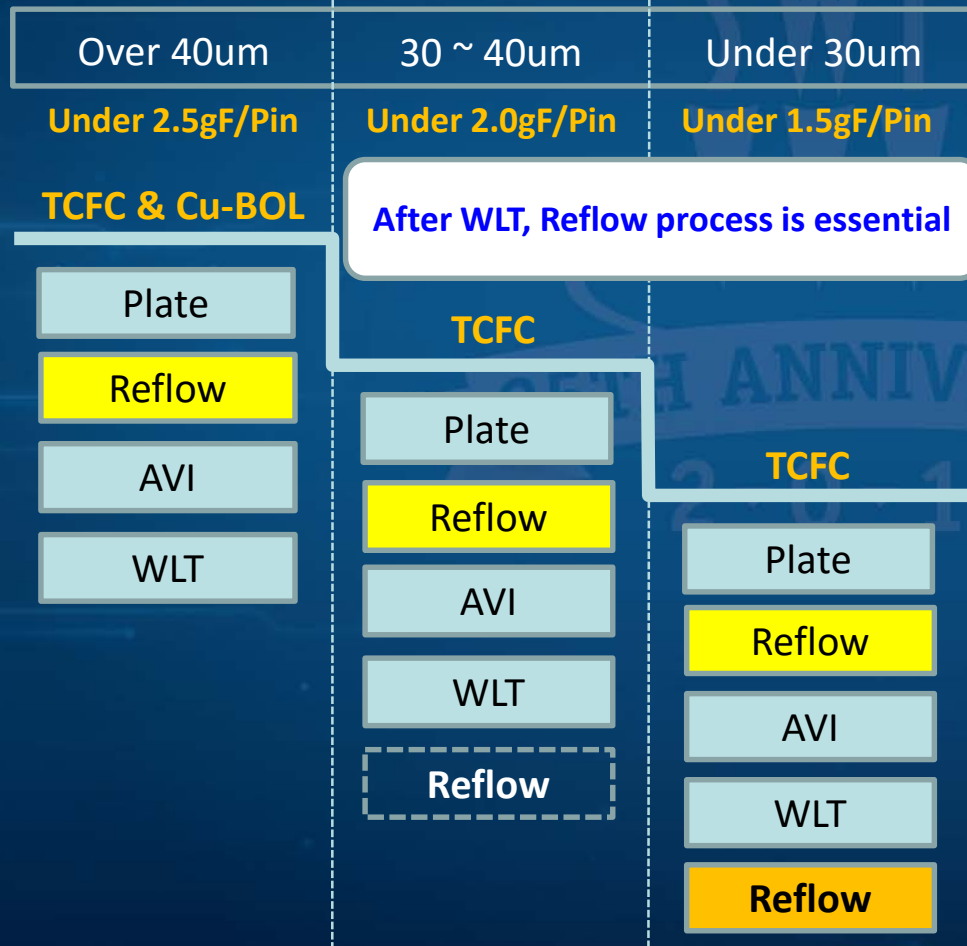
Contact Interface	Aluminum Pad	Cu Pillar without Solder Cap
Figure		
Design Cost	High (extra area overhead)	Low
Probing Decision	✗	✓

- **Essential Item**
→ Cu-P of under 30um diameter need to Reflow process after probing
- **Idea** : without Solder Cap = Cu-P before Reflow
- **Cost Improve**(Bump ~ WLT)
→ Reflow step change

Process change for cost reduction

B. Cu-P Process & Small Diameter Cu-P

Solder Cap Diameter \dashrightarrow



- **Smaller Solder Cap Challenge**

- . Cap Disturbance
- . Solder Stick-Out
- . Heavy Probing \rightarrow Height shortfall
- . Low Force Tip Development (~Keep on C.C.C)

- **2'nd Reflow Process**

- . Back End (Bump ~ WLT) Cost Increase
- . Daily Productivity Drop
- . After 2'nd Reflow Process, Inspection Step

Process change for cost reduction

Present Process

Plate

Reflow

AVI

WLT



← SnAg →

← Copper →

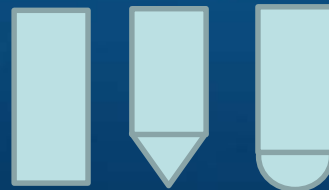
New Process

Plate

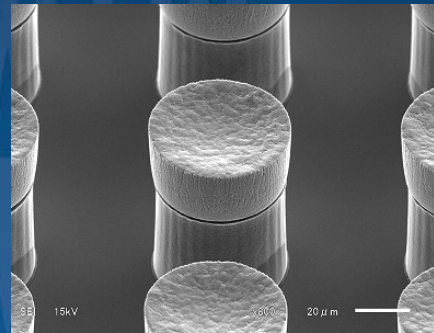
WLT

Reflow

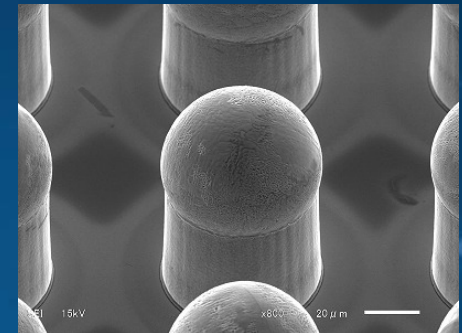
AVI



Before Reflow



After Reflow



Source : DIPSOL Website Figure

<http://www.dipsol-jp.com/wp-content/uploads/>

Type	Cres	Tip Force	Life Time
MEMS Flat	Bad	Good	Good
MEMS Point	Good	Good	Bad
Wire Point	Good	Middle	Bad
Cobra Flat	Bad	Bad	Good

- Table data is expectation grade (SEC Simulation)
→ Next Step Study

SEC Requirement of Flip-Chip Probing

Items	SOLDER			Cu-Pillar				
Pitch	150um ↑	140-149um	135um ↓	135um ↑		110-135um	80-100um	65-80um
Solder Diameter	90um ↑	80um	70um	50um	45um	45um	30um	25um
Needle Diameter	60~75Φ	60-75Φ	50~65Φ	50Φ ↓		45*45um ↓	30*30um ↓	25*25um ↓
Needle Type	Wire	Wire	Wire	Wire (Only Room Temp)		MEMS & Etc	Only MEMS	Only MEMS
Needle Shape	Flat	Flat	Flat	Flat		Flat	Flat (Point)	Flat (Point)
Tip Force (3mil)	7g ↓	6g ↓	4.5g ↓	2.5g ↓		2g ↓	1.5g ↓	1.5g ↓
C.C.C	800[mA] ↑			800[mA] ↑				

- In Solder Ball type, SEC will be using wire type Probe Card for long life realization
 - SEC Case : 2.0 ~ 2.5 Million Touch Down per 1 Probe Card
- Under 100um Cu-P product will be considering process change and MEMS point type

MEMS vertical probe - long life challenge

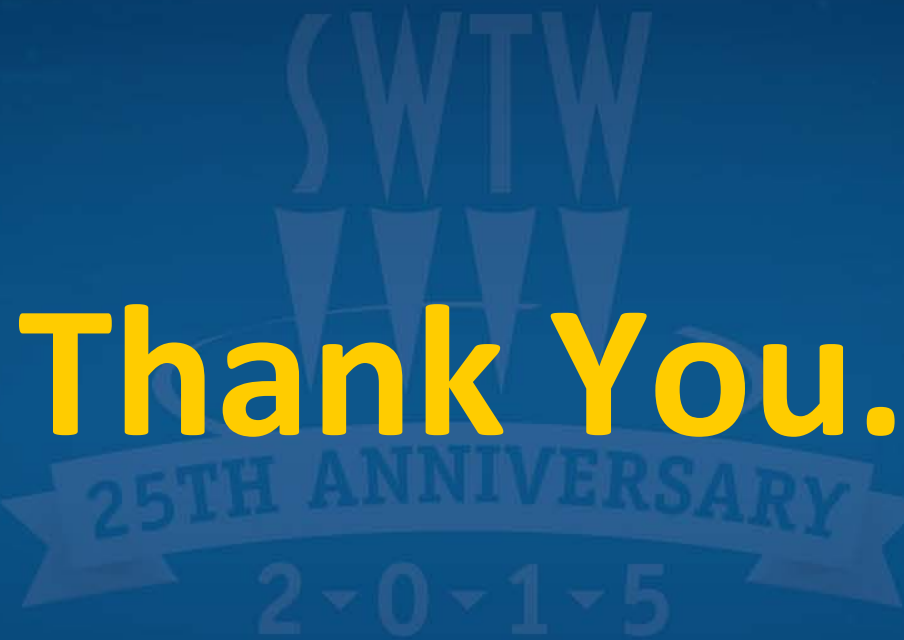
- Usable Budget extension of Probe tip Length
 - Present Level : 300K ~ 500K T/D → Goal : 1,000K T/D (~ 2016.03)
 - Usable Budget of Tip Length : 250 ~ 270um → Goal : 350um (~ 2016.06)
- Probe tip Cleaning Optimization
 - Cleaning Methodology : Polishing Pattern change (~ 2x Improved)
 - Cleaning Sheet : 1um Lapping Film & Abrasive Material change (~ 2x Improved)
 - Minimal Side Length : Tip Diameter 90% (~ 1.5x Improved)
- Probe tip Geometry & Materials Improvement
 - SEC Goal : 1.5 ~ 2.0 Million Touch Down per 1 Probe Card (~ 2017.01)
 - SEC will consistently try to collaborate of Probe Card Maker
for new materials & new concept

Summary

- **Probe card cost for Cu-P probing is higher than Solder Ball type and is increasing continued by small pitch & small diameter**
 - . 130um pitch (cost 20% ↑/pin) → 80um (20~30% ↑/pin) → 65um (?)
- **Cu-P product of over 45um diameter can use Cobra 2.0 & reduction cost**
 - . 7~8\$/pin Cost Reduction : Needle Cost + Extension Life time (SEC Case)
 - . Depends on Factors : Test Temperature, Solder Cap Diameter
- **For more longer life time & more lower cost, Cu-P process change & tip material development should be evaluation**

Next Step

- **By change of Cu-P process, 2'nd reflow process can skip and probe card type flexibility is able to raise (Challenge Subject)**



Thank You.